

SEMICONDUCTOR®

# BC337/338

## **Switching and Amplifier Applications**

• Suitable for AF-Driver stages and low power output stages

Complement to BC327/BC328



# NPN Epitaxial Silicon Transistor

## Absolute Maximum Ratings T<sub>a</sub>=25°C unless otherwise noted

| Symbol                           | Parameter                   | Value     | Units |
|----------------------------------|-----------------------------|-----------|-------|
| V <sub>CES</sub>                 | Collector-Emitter Voltage   |           |       |
|                                  | : BC337                     | 50        | V     |
|                                  | : BC338                     | 30        | V     |
| V <sub>CEO</sub>                 | Collector-Emitter Voltage   |           |       |
|                                  | : BC337                     | 45        | V     |
|                                  | : BC338                     | 25        | V     |
| V <sub>EBO</sub>                 | Emitter-Base Voltage        | 5         | V     |
| I <sub>C</sub>                   | Collector Current (DC)      | 800       | mA    |
| I <sub>C</sub><br>P <sub>C</sub> | Collector Power Dissipation | 625       | mW    |
| TJ                               | Junction Temperature        | 150       | °C    |
| T <sub>STG</sub>                 | Storage Temperature         | -55 ~ 150 | °C    |

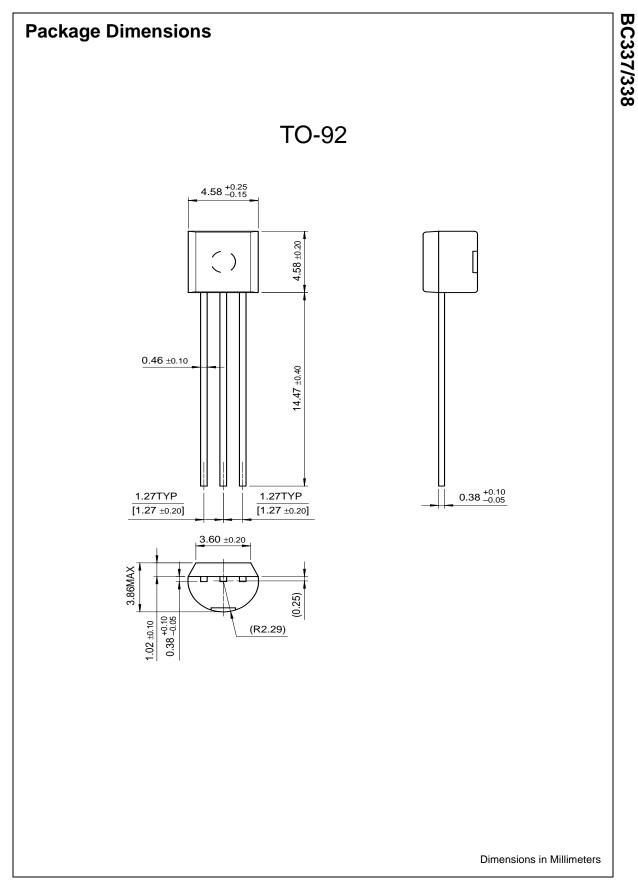
# Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

| Symbol                | Parameter                            | Test Condition                                     | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|--|------|------|------|-------|
| BV <sub>CEO</sub>     | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> =10mA, I <sub>B</sub> =0            |      |      |      |       |
|                       | : BC337                              | -  | 45   |      |      | V     |
|                       | : BC338                              |  | 25   |      |      | V     |
| BV <sub>CES</sub>     | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> =0.1mA, V <sub>BE</sub> =0          |      |      |      |       |
|                       | : BC337                              |  | 50   |      |      | V     |
|                       | : BC338                              |  | 30   |      |      | V     |
| BV <sub>EBO</sub>     | Emitter-Base Breakdown Voltage       | I <sub>E</sub> =0.1mA, I <sub>C</sub> =0           | 5    |      |      | V     |
| I <sub>CES</sub>      | Collector Cut-off Current            |  |      |      |      |       |
|                       | : BC337                              | V <sub>CE</sub> =45V, I <sub>B</sub> =0            |      | 2    | 100  | nA    |
|                       | : BC338                              | V <sub>CE</sub> =25V, I <sub>B</sub> =0            |      | 2    | 100  | nA    |
| h <sub>FE1</sub>      | DC Current Gain                      | V <sub>CE</sub> =1V, I <sub>C</sub> =100mA         | 100  |      | 630  |       |
| h <sub>FE2</sub>      |                                      | V <sub>CE</sub> =1V, I <sub>C</sub> =300mA         | 60   |      |      |       |
| V <sub>CE</sub> (sat) | Collector-Emitter Saturation Voltage | I <sub>C</sub> =500mA, I <sub>B</sub> =50mA        |      |      | 0.7  | V     |
| V <sub>BE</sub> (on)  | Base Emitter On Voltage              | V <sub>CE</sub> =1V, I <sub>C</sub> =300mA         |      |      | 1.2  | V     |
| f <sub>T</sub>        | Current Gain Bandwidth Product       | V <sub>CE</sub> =5V, I <sub>C</sub> =10mA, f=50MHz |      | 100  |      | MHz   |
| C <sub>ob</sub>       | Output Capacitance                   | V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz    |      | 12   |      | pF    |

# h<sub>FE</sub> Classification

| Classification   | 16        | 25        | 40        |
|------------------|-----------|-----------|-----------|
| h <sub>FE1</sub> | 100 ~ 250 | 160 ~ 400 | 250 ~ 630 |
| h <sub>FE2</sub> | 60-       | 100-      | 170-      |
|                  |           |           |           |

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|---|---|---|--|
| Programmable Active Droop™  | OPTOPLANAR™   | SMART START™  |  |

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|--------------------------|---------------------------|---|
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